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Thermally aware high-power inverter board for battery-powered applications

Prospero LOMBARDI

Introduction



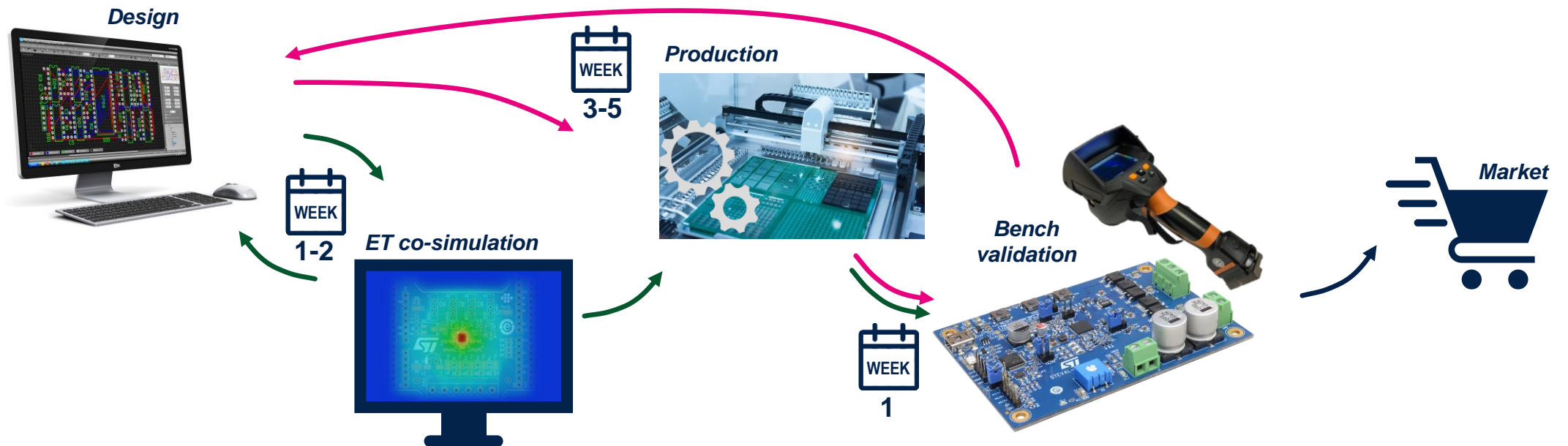
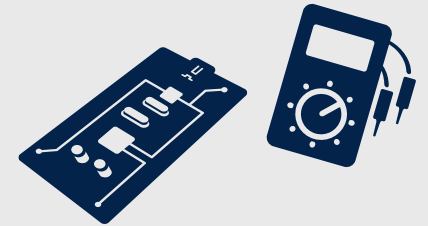
High power at low voltage

Best efficiency and reliability

Compact form factor

but...

Challenging PCB design



We are creators and makers of technology



One of the world's largest semiconductor companies



48,000 employees of which
8,400 in R&D



\$12.8 billion revenues
in 2021



Over **80** sales & marketing
offices serving over **200,000**
customers across the globe



14 manufacturing sites



Signatory of the United Nations Global Compact (UNGC)
Member of the Responsible Business Alliance (RBA)

ST addresses the industrial market with application driven, high added-value ASSPs & ASICs

Motor control leadership areas



STDRIVE
3-phase drivers

**Motion 3-phase
Low Voltage**

Best-in-class motor driving,
high efficiency and low
consumption



STGAP
Galvanic Driver

**Safety &
High voltage**

6 kV galvanic isolated
drivers optimized for SiC,
GaN & IGBT



STSPIN32

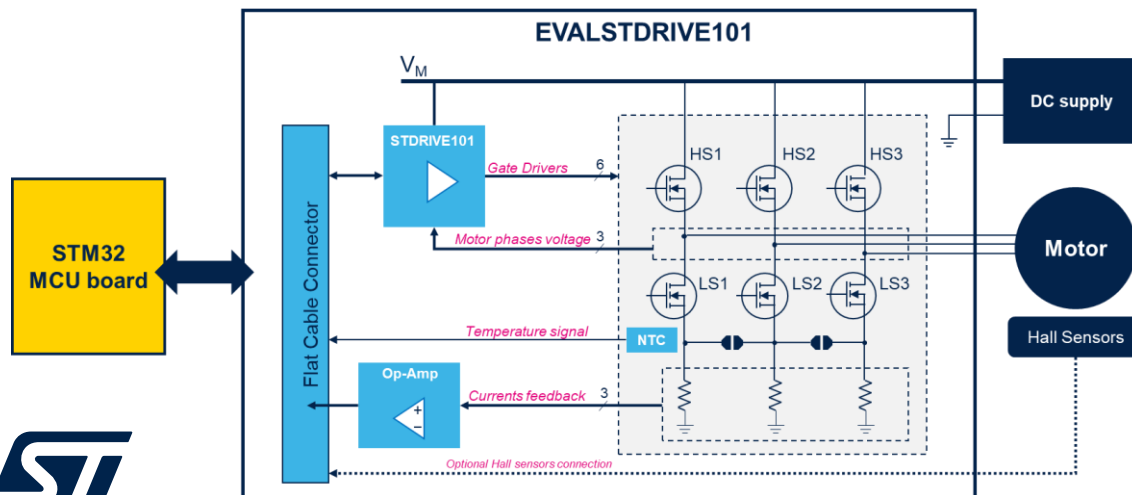
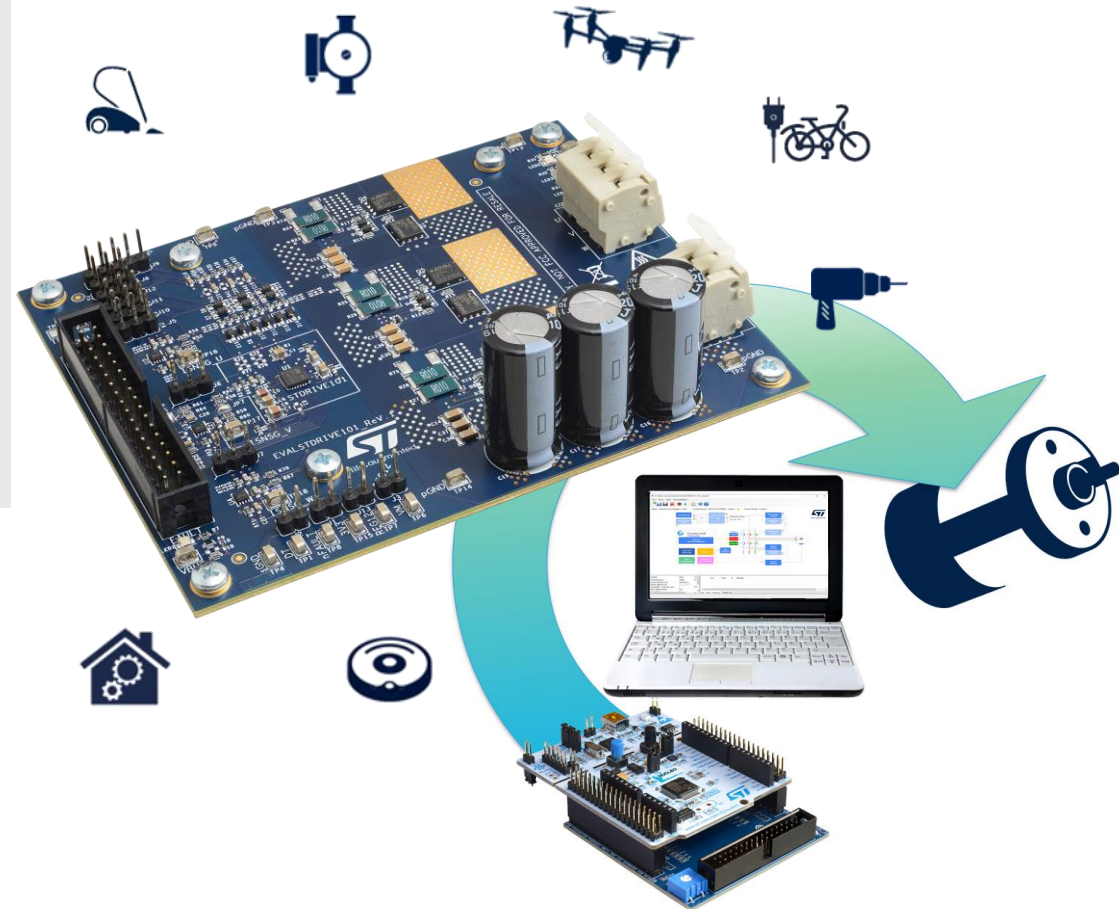
Digital motion

High system integration,
Flexibility, performance



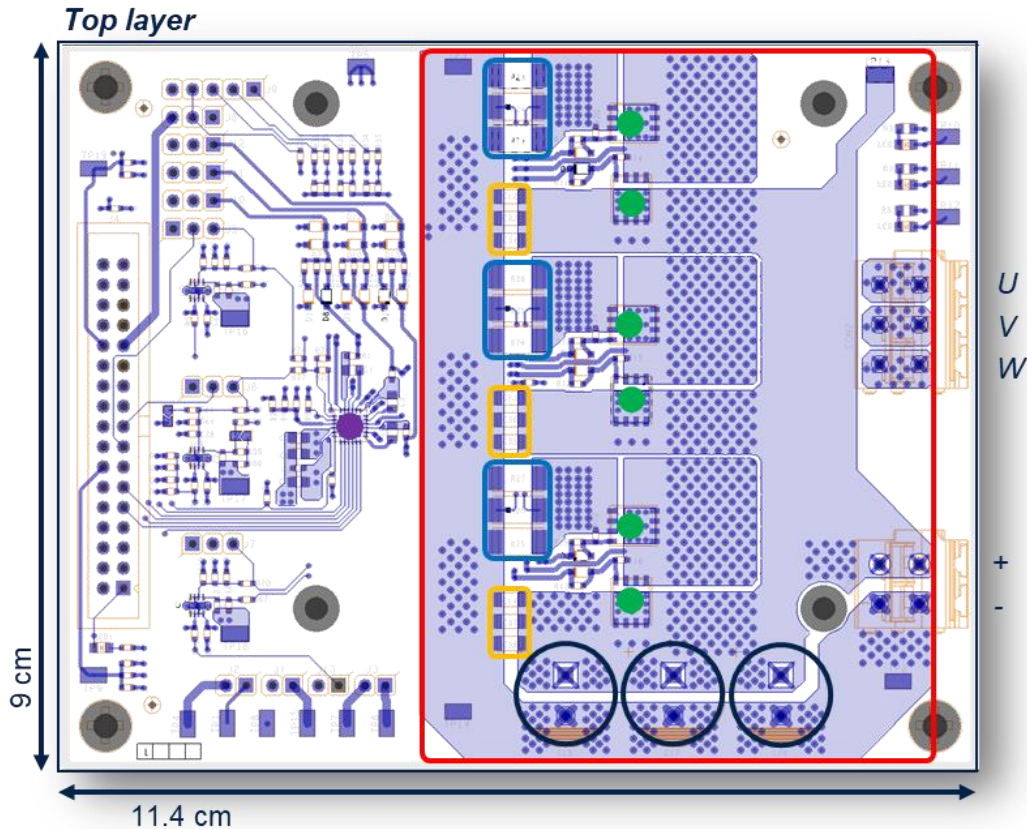
EVALSTDRIVE101

- STDRIVE101 gate driver and STL110N10F7 MOSFETs
- $15A_{rms}$ output current ($20A_{rms}$ with heatsink) at 75V
- Three or single shunt
- Sensor and sensor less algorithms
- Bus voltage and temperature monitoring
- Overcurrent / short circuit protection
- NUCLEO board interfacing
- Free software libraries





Layout improvements



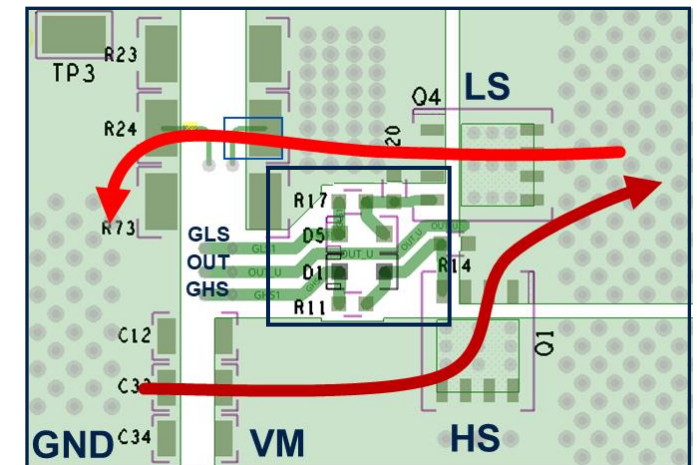
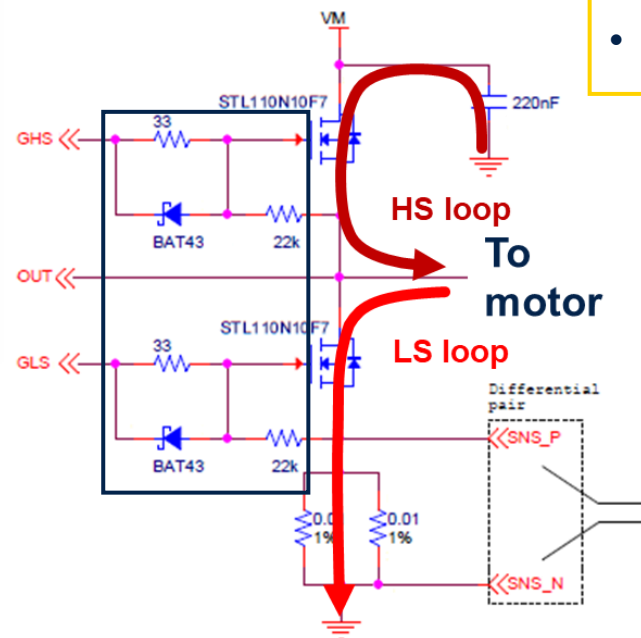
- STDRIVE101
- STL110N10F7
- 50 cm² power stage
- Shunt resistors
- Ceramic capacitors
- Electrolytic capacitors



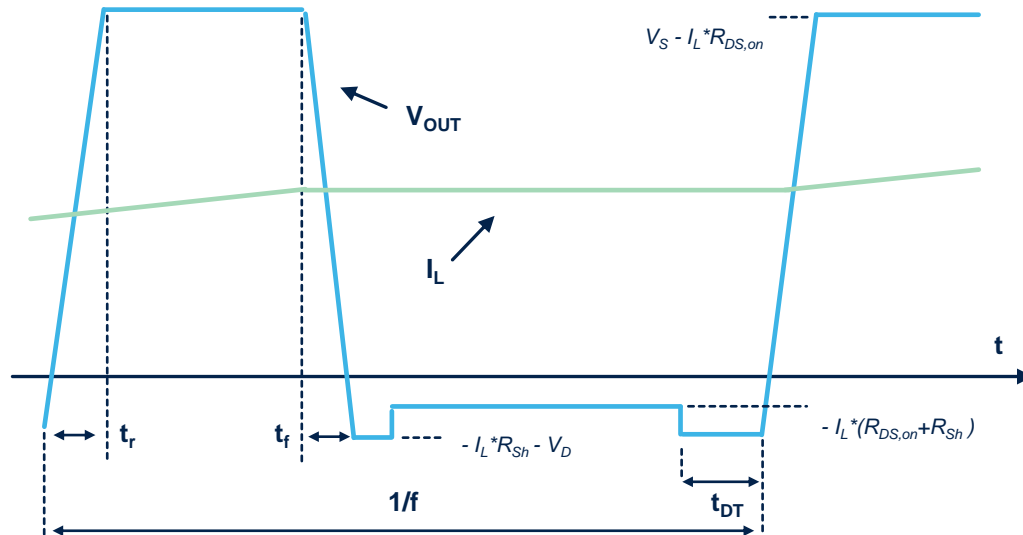
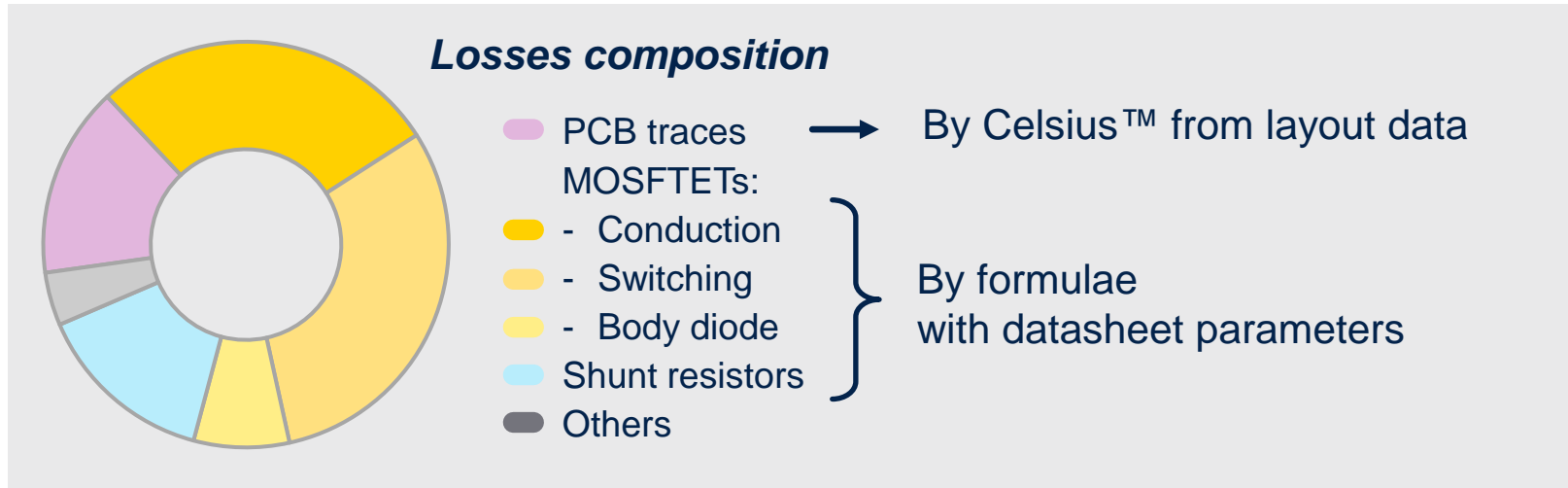
- Better heat spreading
- Max dissipation area
- Dual side cooling



- Reduced current density
- Small loops placement
- Fast switching



Estimate of power losses



551 mW

$$P_{cond} \sim \frac{R_{on} \cdot I_L^2 \cdot (1 - 2 \cdot t_{dt} \cdot f)}{2}$$

602 mW

$$P_{sw} \sim \frac{f \cdot V_s \cdot I_L \cdot \left(\frac{Q_p \cdot R_g}{V_{gd} - V_p} + \frac{Q_p}{I_{gd}} + R_g \cdot C_{iss} \cdot \ln \left(\frac{V_{gd} - V_{th}}{V_{gd} - V_p} \right) + \frac{C_{iss} \cdot (V_p - V_{th})}{I_{gd}} \right)}{4}$$

150 mW

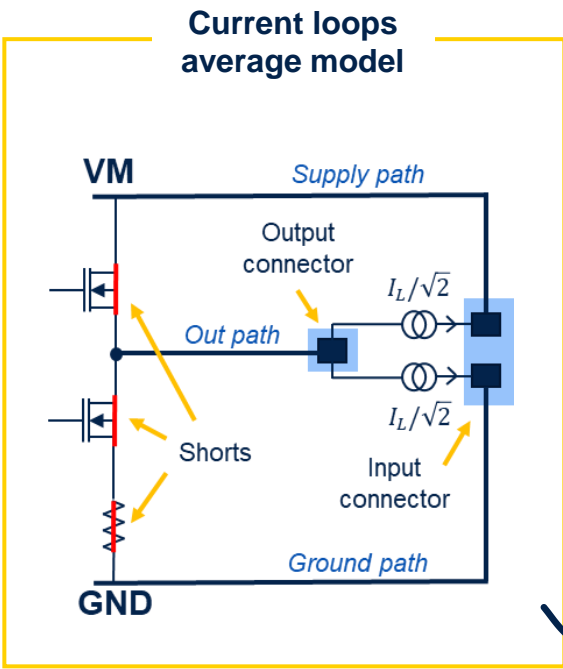
$$P_{dt} \sim V_d \cdot I_L \cdot t_{dt} \cdot f$$

281 mW

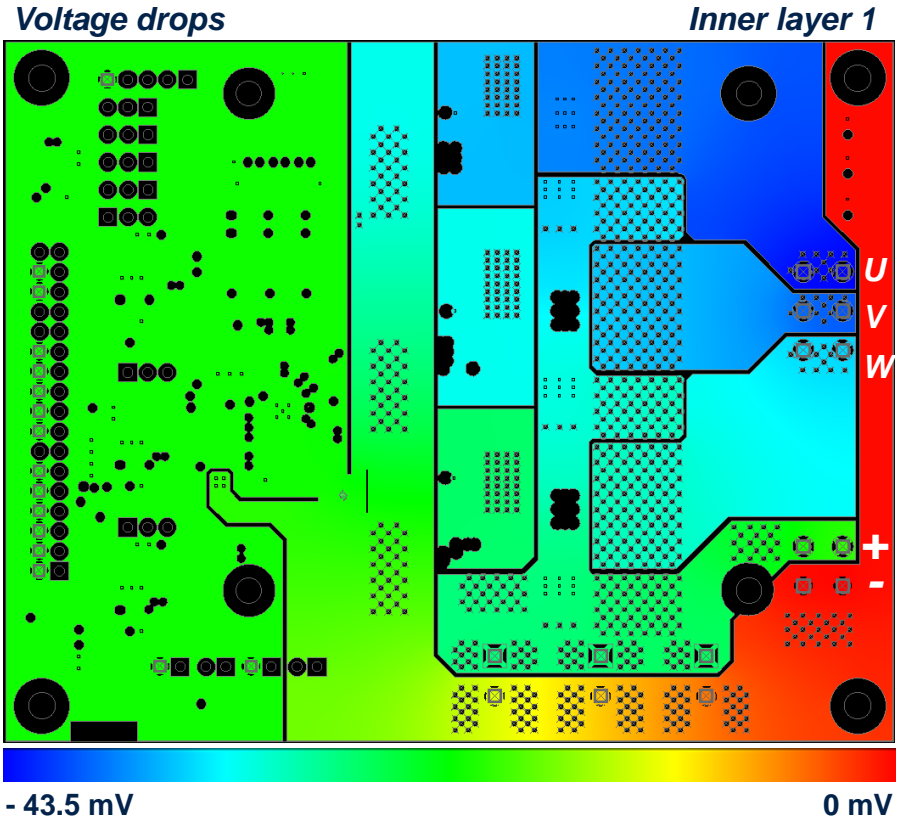
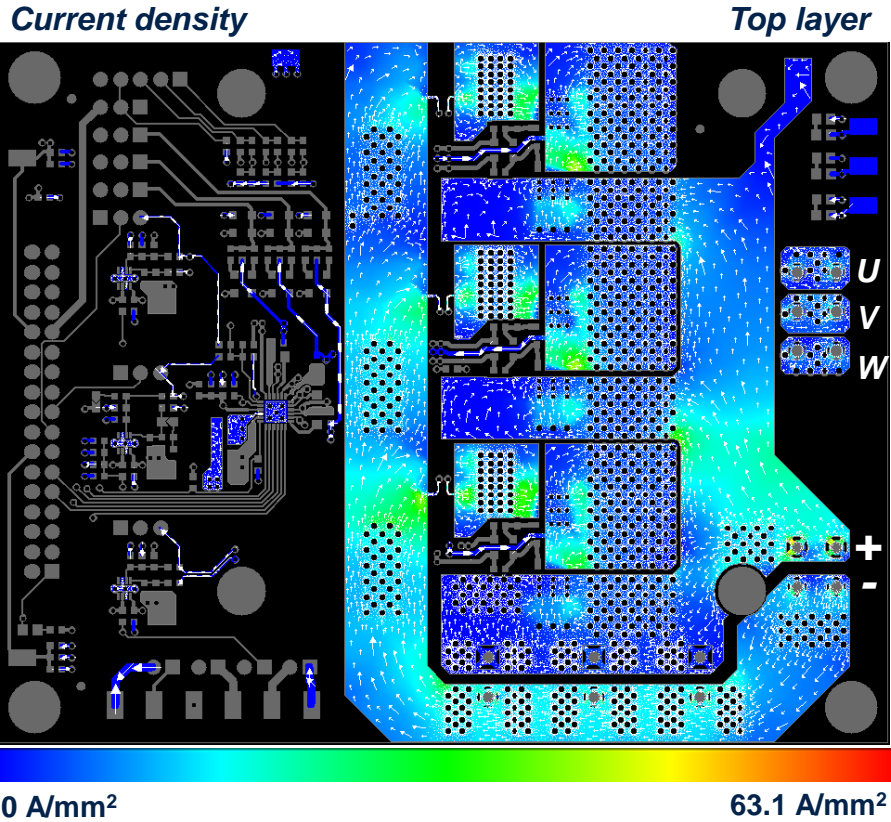
$$P_{sh} = \frac{R_{sh} \cdot I_L^2}{2}$$

Celsius simulation

Electrical analysis @ 15 A_{rms}



Only effects on traces

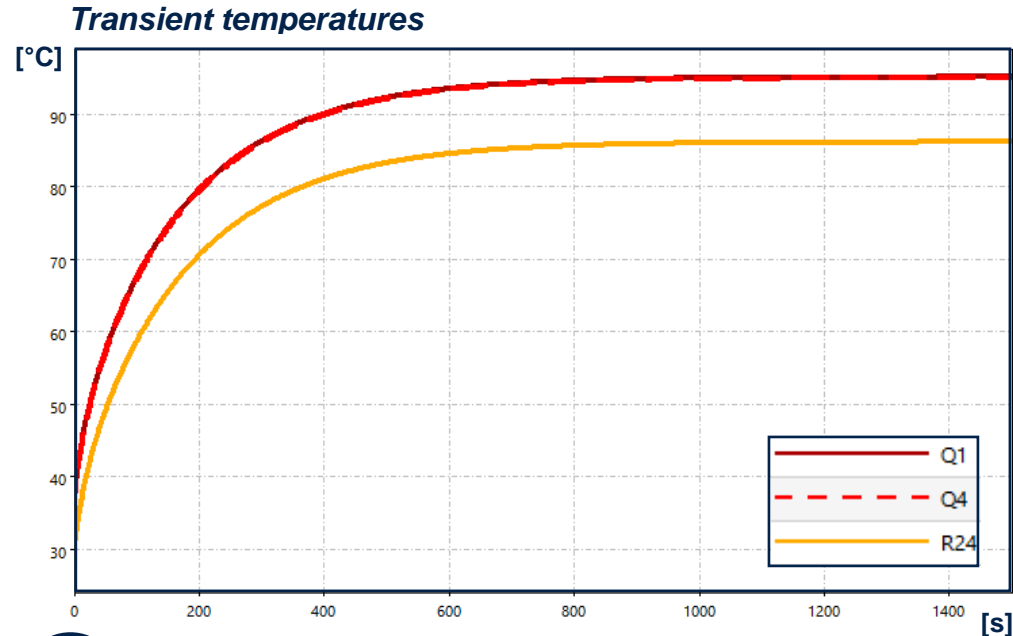
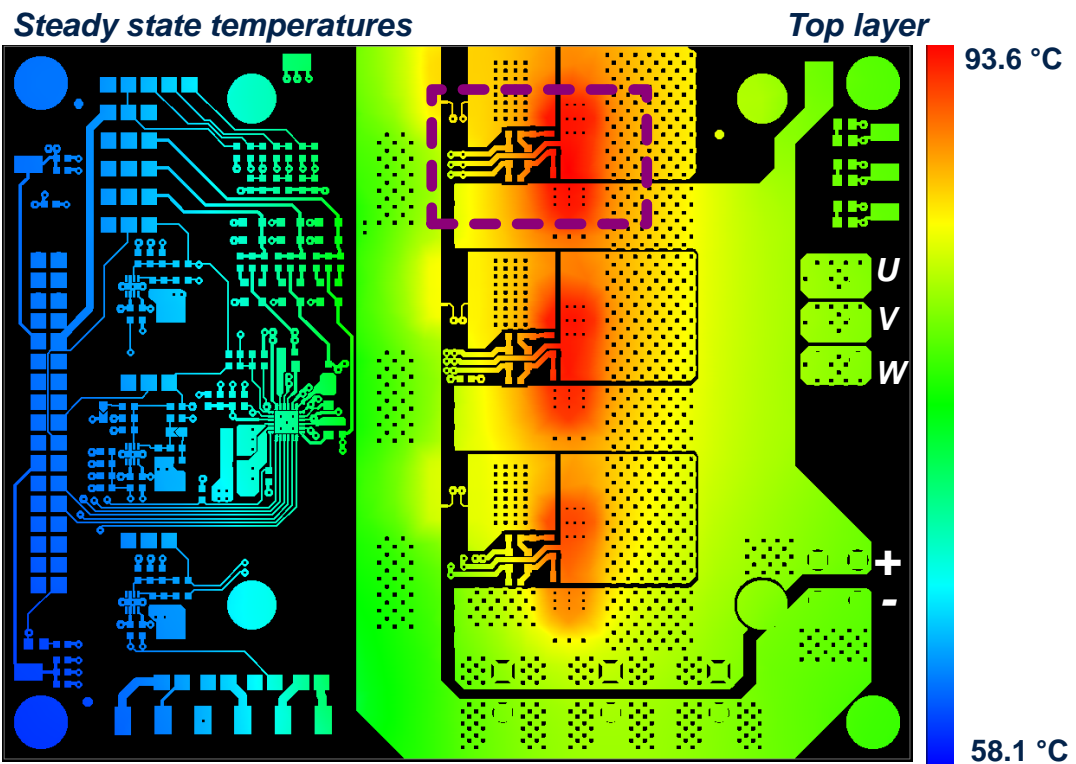


- Current density below 25 A/mm²
- Hotspots not of concern
- No bottleneck and balanced outputs

Celsius simulation

Thermal analysis @ 15 A_{rms}

- Settings**
- 28 °C ambient temperature
 - Fixed heat transfer coefficients
 - 2-R model for MOSFETs
 - Step functions for sources

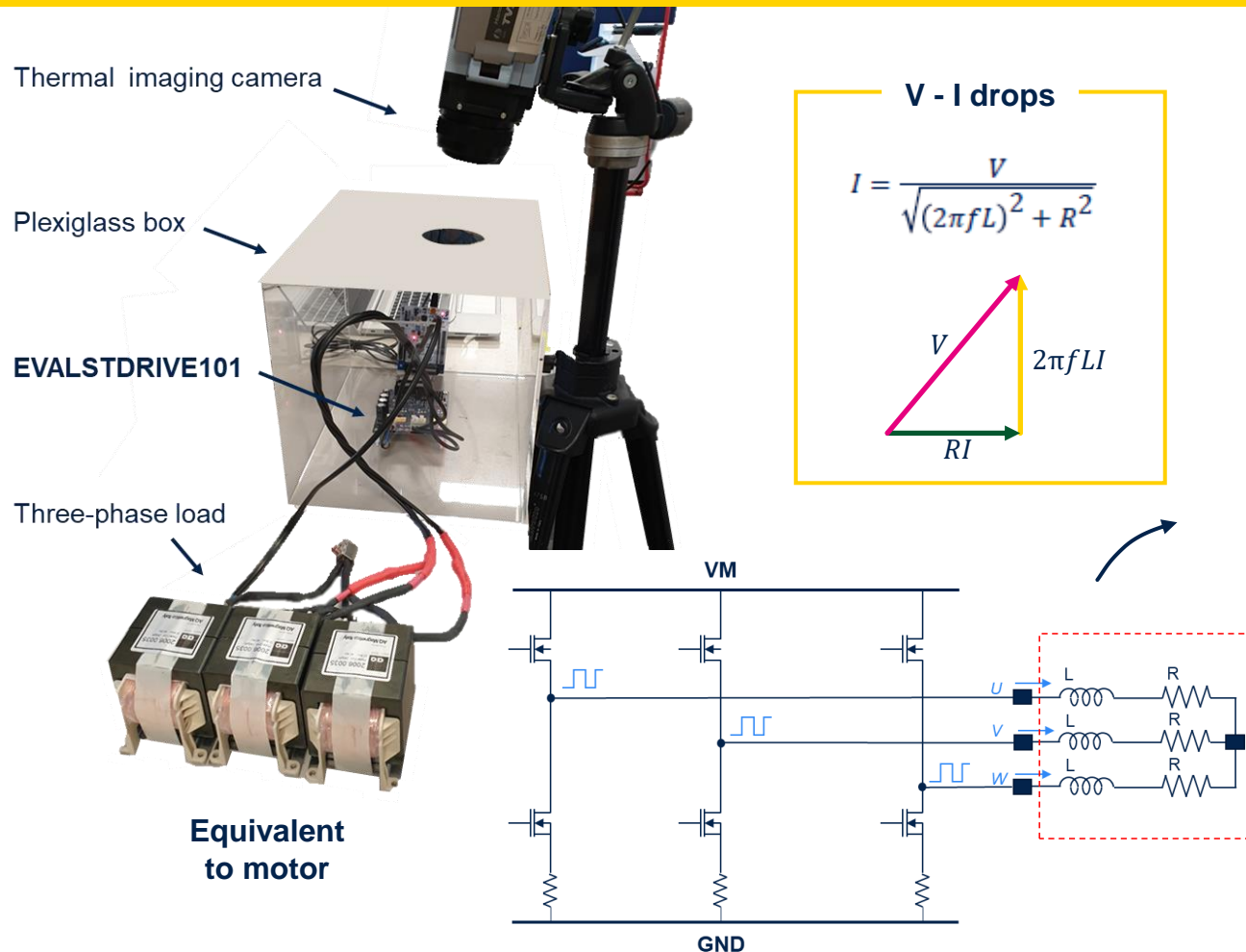


- Hottest U half bridge
- MOSFETs at 95 °C and shunts at 86 °C
- 13 minutes warm up
- 5 °C delta - top vs bottom

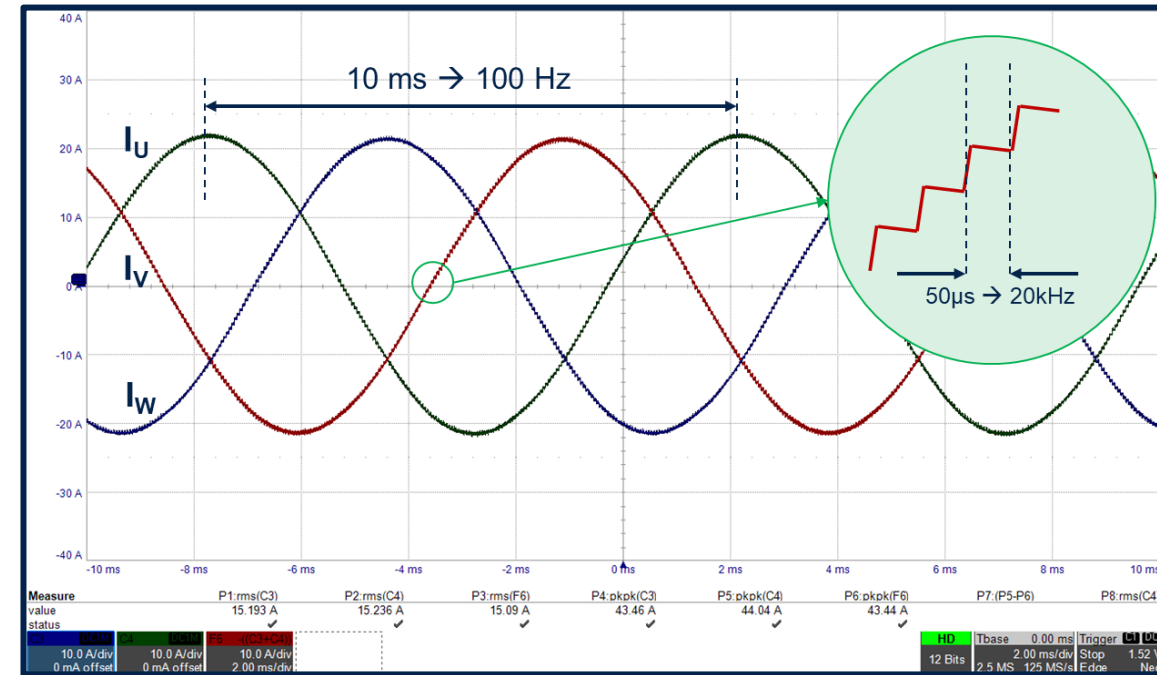
Very good design margin

Bench validation

Setup description



Configurable sinusoidal currents



- Power stage as in application
- Easier to implement
- Fast tuning

Bench validation

Power losses measurement



Correlate estimated data with real losses

$$P_{loss} = P_{in} - P_{out} = \overline{V_{in} \cdot I_{in}} - \sum_{i=1}^3 \overline{(V_i - V_c) \cdot I_i}$$

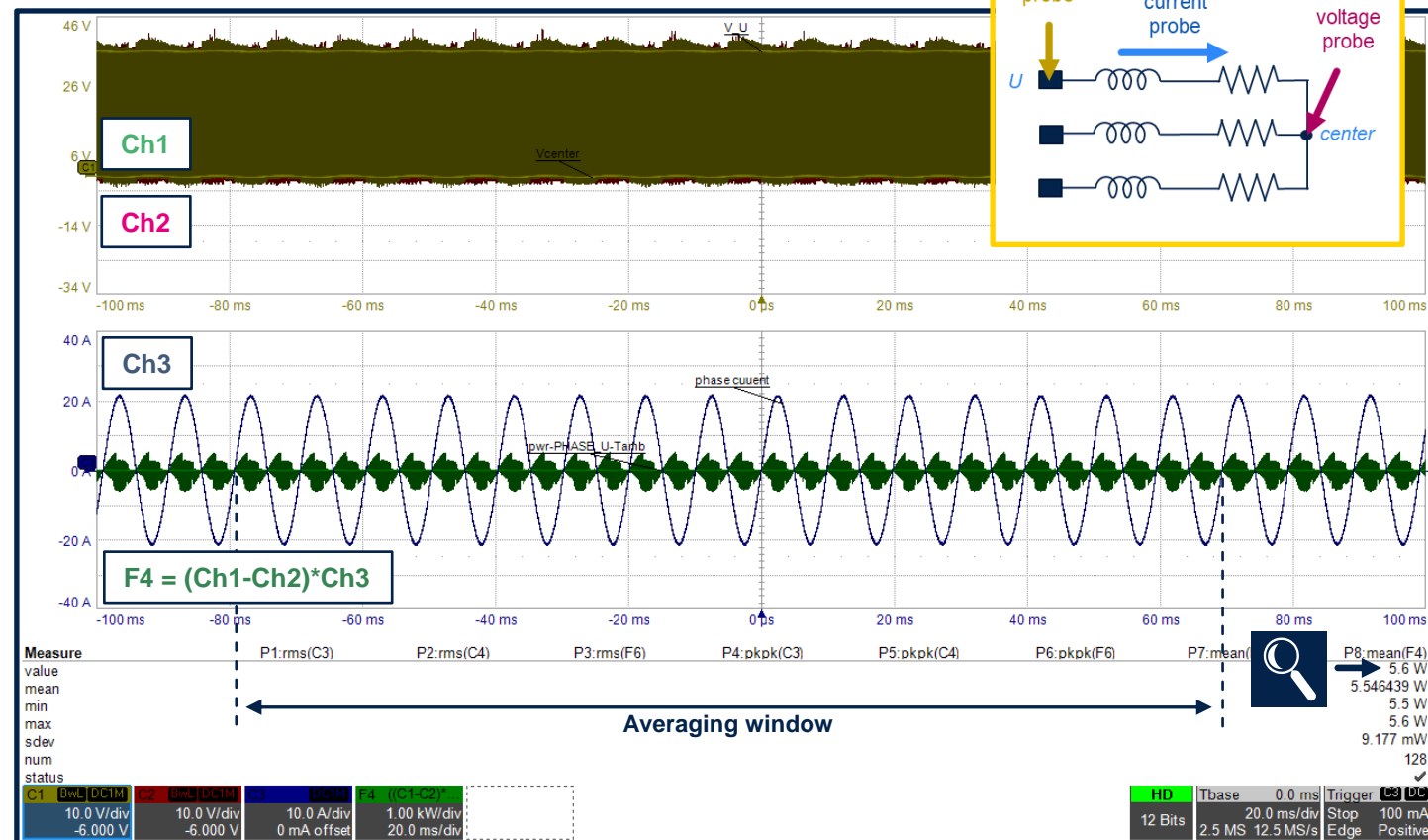
By oscilloscope

Power	Estimate [W]	Measure @ T _{amb} [W]	Measure @ T _{hot} [W]
P_{in}	-	27.51	28.39
P_{out}^U	-	5.6	5.7
P_{out}^V	-	6.5	6.6
P_{out}^W	-	6.1	6.2
P_{loss}	9.5	9.36	9.89



- Spread hot vs ambient
- Slight load unbalancing
- Estimate in line with measures

U half-bridge losses



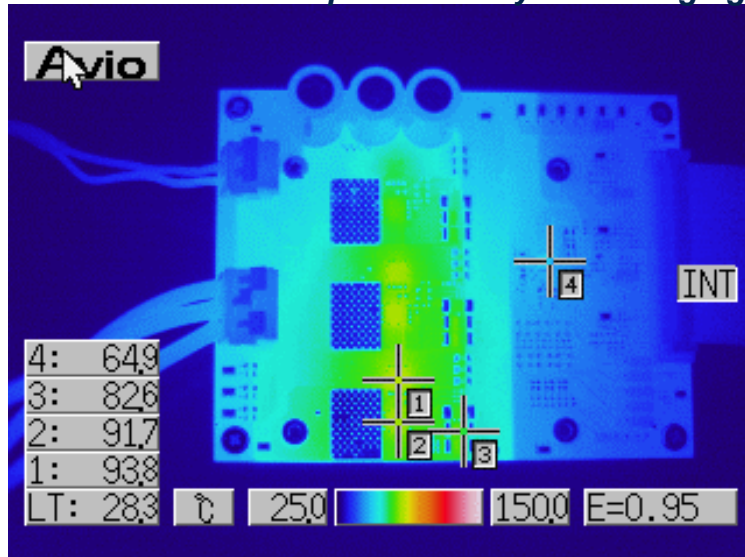
Bench validation

Thermal characterization

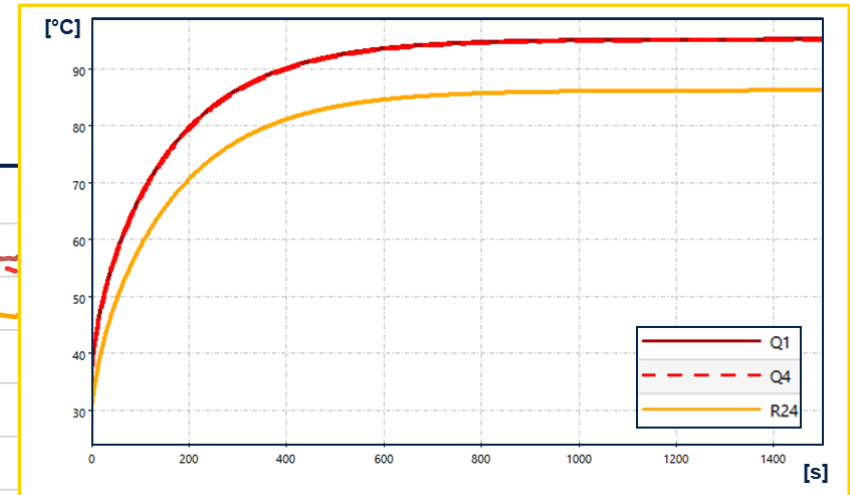
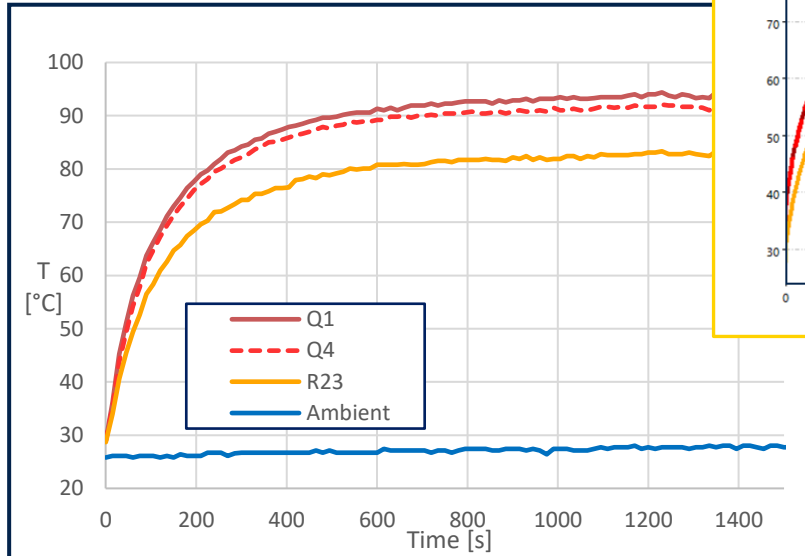


Correlate simulations
with real heating

Top side steady state imaging



Half-bridge U components warm up



Simulated transient temperatures

Component	Simulation [°C]	Measure [°C]
HS MOSFET Q1	95.1	93.8
LS MOSEFT Q4	94.9	91.7
Shunt resistor R23	86.3	82.6



- Confirmed hottest half bridge
- Same transient
- Very good temperatures matching



Conclusions

EVALSTDRIVE101 optimized by Celsius™

High power & low voltage BLDC motors
Battery-powered applications

- Fine tuned layout
- Detailed voltage drops and current density
- Foreseen temperature profile and hotspots
- Certified performance by thermal imaging

Find more on:

https://www.st.com/resource/en/technical_article/ta0361-thermally-aware-highpower-inverter-board-for-batterypowered-applications--stmicroelectronics.pdf
https://www.cadence.com/content/dam/cadence-www/global/en_US/documents/tools/system-analysis/secured/thermally-optimizing-a-high-power-pcb.pdf

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STDRIVE101

75 V 3-phase low voltage brushless gate driver



Compactness

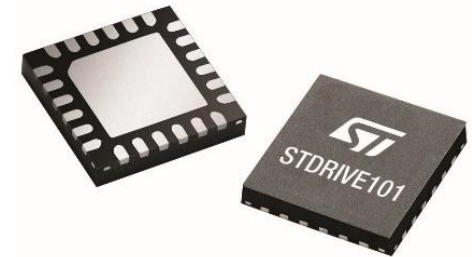
- Compact design with 4x4mm QFN
- Integrated bootstrap diodes

Robustness

- VDS monitoring for each Power MOSFET
- Fully protected (UVLO, OCP, Thermal shutdown)
- nFAULT open-drain for fault signaling

Performance

- Operating Voltage: 5.5 V to 75 V
- I = 600 mA sink/source driving capability
- 12 V LDO embedded
- Two Flexible inputs driving: Enable / Input with adjustable dead-time generation or Direct driving with interlocking
- Very short 70 ns propagation delay / 20 ns phases matching
- Standby mode for low consumption



VFQFPN4x4 24 leads

Key applications

- Power tools
- E-bike
- Drones, Robotics
- Home appliance, Air purifiers
- Fans